

AMENDMENTS TO THE SPECIFICATION

- Please amend the Title which begins on page 1, line 1, as follows:

~~THYRISTOR-BASED SRAM AND METHOD USING QUASI-PLANAR  
DOUBLE GATED FIN FIELD EFFECT TRANSISTOR FINFET-PROCESS  
FOR THE FABRICATION-THEREOF OF A THYRISTOR-BASED  
STATIC READ/WRITE RANDOM-ACCESS MEMORY~~